

L Number	Hits	Search Text	DB	Time stamp
	2967	((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:12
	660	((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:14
	387	(((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and ((trench same isolation) or sti or (shallow adj trench adj isolation)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:15
	256	(((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and ((trench same isolation) or sti or (shallow adj trench adj isolation))) and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:16
	187	((((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and ((trench same isolation) or sti or (shallow adj trench adj isolation))) and polysilicon) and (thick or thickness) and (depth or deep)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:16
	99	((((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and ((trench same isolation) or sti or (shallow adj trench adj isolation))) and polysilicon) and (thick or thickness) and (depth or deep)) and (cmp or (chemical adj mechanical adj planariz\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:19
	1327	(EVANS same DAVID) or (HSU same (SHENG or TENG)) or (ULRICH same BRUCE) or (TWEET same DOUGLAS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:22
	1327	(EVANS same DAVID) or (HSU same (SHENG or TENG)) or (ULRICH same BRUCE) or (TWEET same DOUGLAS) or (STECKER same LISA)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:23
	98	((EVANS same DAVID) or (HSU same (SHENG or TENG)) or (ULRICH same BRUCE) or (TWEET same DOUGLAS) or (STECKER same LISA)) and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:23
	37	((((EVANS same DAVID) or (HSU same (SHENG or TENG)) or (ULRICH same BRUCE) or (TWEET same DOUGLAS) or (STECKER same LISA)) and CMOS) and ((trench same isolation) or sti or (shallow adj trench adj isolation)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:23
	33	(((((EVANS same DAVID) or (HSU same (SHENG or TENG)) or (ULRICH same BRUCE) or (TWEET same DOUGLAS) or (STECKER same LISA)) and CMOS) and ((trench same isolation) or sti or (shallow adj trench adj isolation))) and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:24

19	(((((EVANS same DAVID) or (HSU same (SHENG or TENG)) or (ULRICH same BRUCE) or (TWEET same DOUGLAS) or (STECKER same LISA)) and CMOS) and ((trench same isolation) or sti or (shallow adj trench adj isolation))) and polysilicon) and (cmp or (chemical adj mechanical adj planariz\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:24
9	(((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and ((trench same isolation) or sti or (shallow adj trench adj isolation))) and polysilicon) and (thick or thickness) and (depth or deep)) and (cmp or (chemical adj mechanical adj planari2\$5))) and (alignment same (mark\$3 or key))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:25